



## General Description

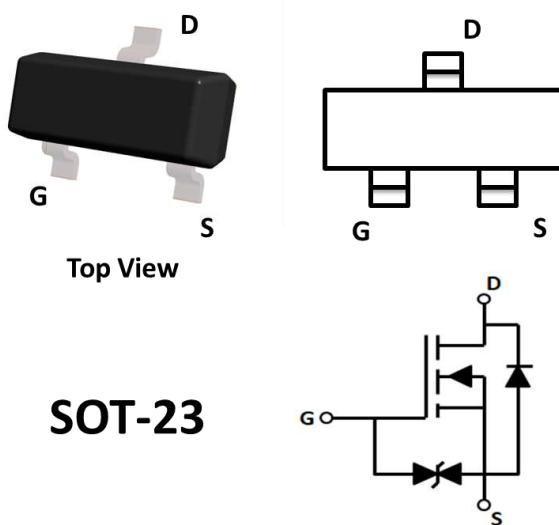
- Trench Power LV MOSFET technology
- High Power and current handing capability
- ESD Protected Up to 3.5KV (HBM)

## Applications

- PWM application
- Load switch

## Product Summary

$V_{DS}$	20	V
$R_{DS(on),Typ} @ V_{GS}=4.5\text{ V}$	16	$\text{m}\Omega$
$I_D$	7.0	A



## Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	$V_{DS}$	20	V
Gate-source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current	$I_D$	7.0	A
		5.6	
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	28	A
Total Power Dissipation @ $T_A=25^\circ\text{C}$	$P_D$	1.3	W
Thermal Resistance Junction-to-Ambient @ Steady State	$R_{\theta JA}$	96	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	$^\circ\text{C}$



ASCENDSEMI

ASDM3416EZA

20V N-Channel MOSFET

Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	20			V
Zero Gate Voltage Drain Current	$I_{\text{DS}S}$	$V_{\text{DS}}=20\text{V}, V_{\text{GS}}=0\text{V}$			1	$\mu\text{A}$
Gate-Body Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}= \pm 10\text{V}, V_{\text{DS}}=0\text{V}$		2.5	$\pm 10$	$\mu\text{A}$
		$V_{\text{GS}}= \pm 5\text{V}, V_{\text{DS}}=0\text{V}$		300	$\pm 1000$	nA
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	0.45	0.62	1.0	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}= 4.5\text{V}, I_{\text{D}}=7.0\text{A}$		16	18	$\text{m}\Omega$
		$V_{\text{GS}}= 2.5\text{V}, I_{\text{D}}=4.0\text{A}$		19	22	
		$V_{\text{GS}}= 1.8\text{V}, I_{\text{D}}=3.0\text{A}$		25	39	
Diode Forward Voltage	$V_{\text{SD}}$	$I_{\text{S}}=7.0\text{A}, V_{\text{GS}}=0\text{V}$			1.2	V
Maximum Body-Diode Continuous Current	$I_{\text{S}}$				7.0	A
<b>Dynamic Parameters</b>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=10\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$		640		$\text{pF}$
Output Capacitance	$C_{\text{oss}}$			147		
Reverse Transfer Capacitance	$C_{\text{rss}}$			78		
<b>Switching Parameters</b>						
Total Gate Charge	$Q_{\text{g}}$	$V_{\text{GS}}=4.5\text{V}, V_{\text{DS}}=10\text{V}, I_{\text{D}}=7.0\text{A}$		8.1		$\text{nC}$
Gate Source Charge	$Q_{\text{gs}}$			2.4		
Gate Drain Charge	$Q_{\text{gd}}$			3		
Turn-on Delay Time	$t_{\text{D}(\text{on})}$	$V_{\text{GS}}=4.5\text{V}, V_{\text{DD}}=10\text{V}, R_{\text{L}}=1.5\Omega, R_{\text{GEN}}=3\Omega$		1.2		$\text{ns}$
Turn-on Rise Time	$t_{\text{r}}$			2.4		
Turn-off Delay Time	$t_{\text{D}(\text{off})}$			22		
Turn-off Fall Time	$t_{\text{f}}$			7		

A. Pulse Test: Pulse Width  $\leq 300\text{us}$ , Duty cycle  $\leq 2\%$ .

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

## Typical Performance Characteristics

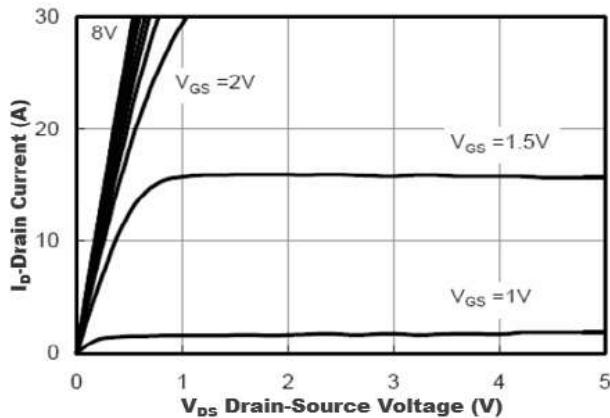


Figure1. Output Characteristics

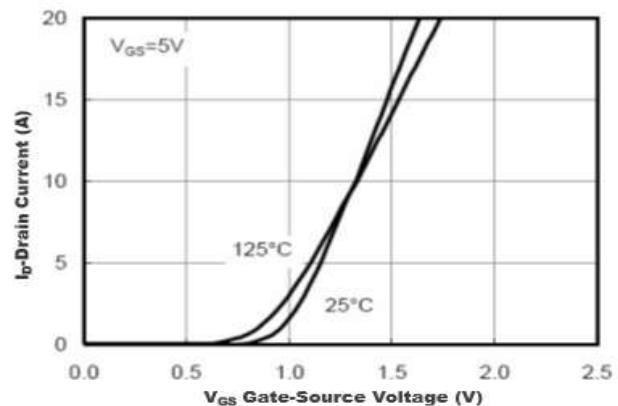


Figure2. Transfer Characteristics

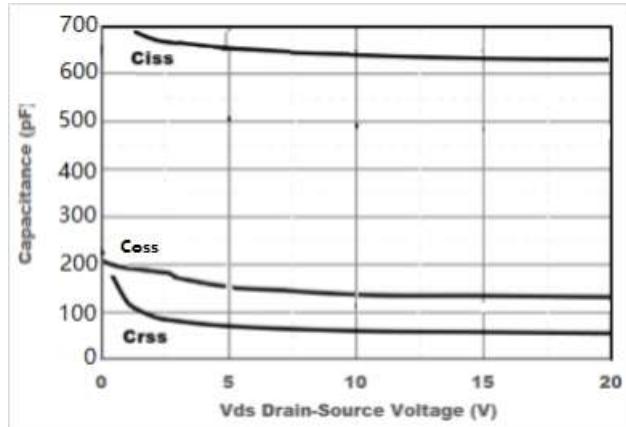


Figure3. Capacitance Characteristics

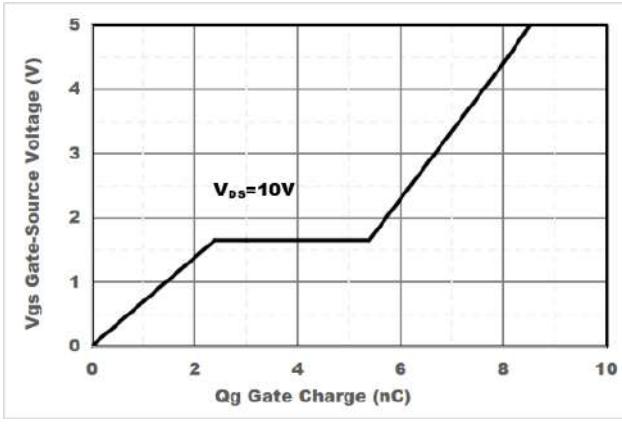


Figure4. Gate Charge

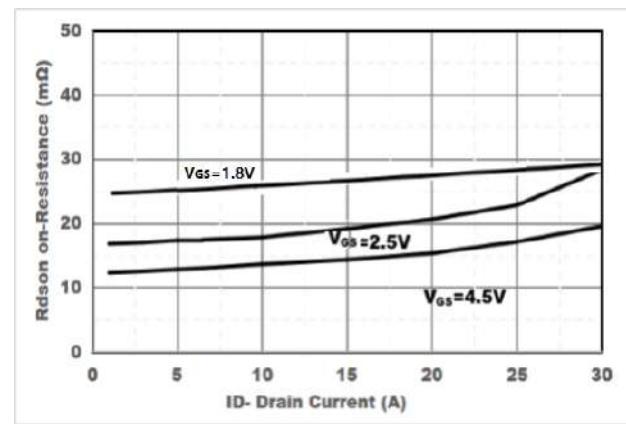


Figure5. Drain-Source on Resistance

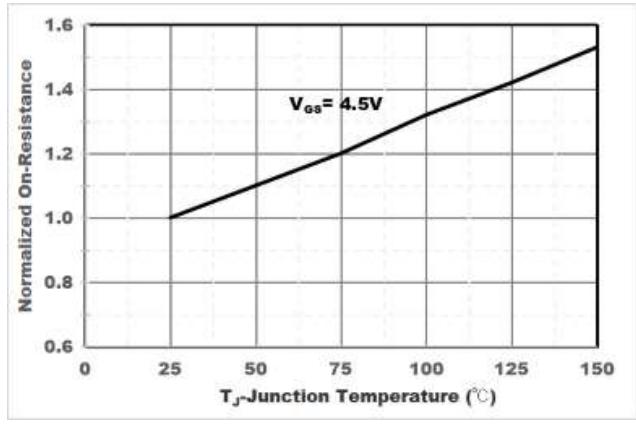


Figure6. Drain-Source on Resistance

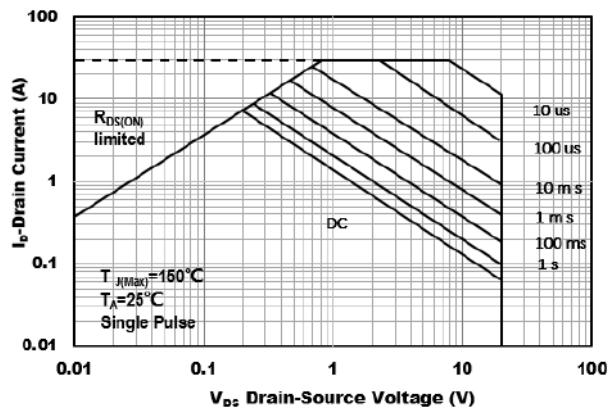


Figure7. Safe Operation Area

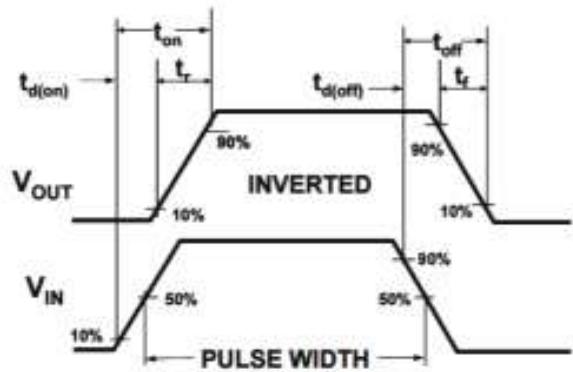
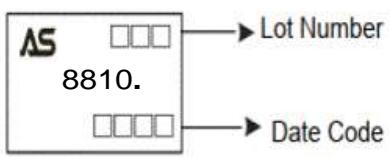


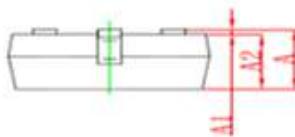
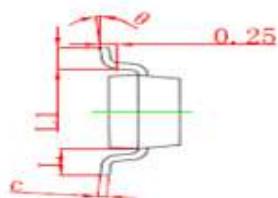
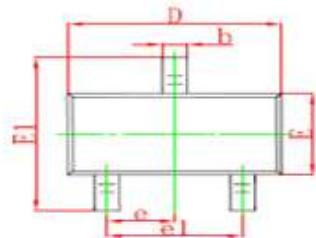
Figure8. Switching wave

## Ordering and Marking Information

Ordering Device No.	Marking	Package	Packing	Quantity
ASDM3416EZA-R	8810.	SOT-23	Tape&Reel	3000/Reel

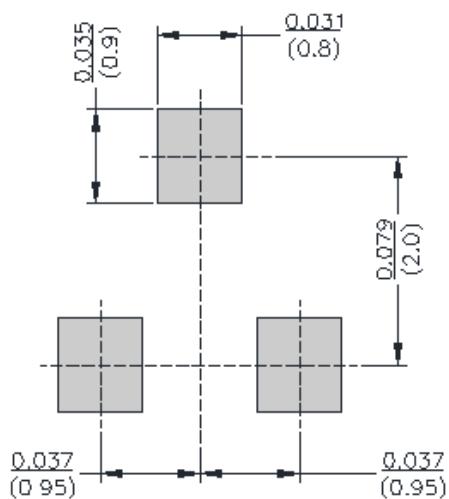
PACKAGE	MARKING
SOT-23	

### SOT-23 Package information



Symbol	Dimensions in Millimeter		Dimensions in Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950Type		0.037Type	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.220REF	
L1	0.300	0.500	0.012	0.020
θ	0 °	8 °	0 °	8 °

### ■SOT-23 Suggested Pad Layout



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